L Number	Hits	Search Text	DB	Time stamp
3	1422619	semiconductor	USPAT;	2004/11/08 14:17
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
4	424825	LED\$1 near3 chip) (light\$3 near3 emitt\$3	USPAT;	2004/11/08 13:27
		. *,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
5	400005	TEDC1 with skim) /light(2 mage) omitt(2	IBM_TDB USPAT;	2004/11/08 13:27
5	426835	LED\$1 with chip) (light\$3 near3 emitt\$3	US-PGPUB;	2004/11/08 13.27
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
6	94753	semiconductor & (LED\$1 near3 chip)	USPAT;	2004/11/08 13:27
		(light\$3 near3 emitt\$3)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		·	IBM_TDB	
7	16037	(GaN nitride) & (semiconductor & (LED\$1	USPAT;	2004/11/08 14:18
and the same of th		near3 chip) (light\$3 near3 emitt\$3))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
8	1843	((GaN nitride) & (semiconductor & (LED\$1	IBM_TDB USPAT;	2004/11/08 14:19
8	1843		US-PGPUB;	2004/11/08 14:19
		near3 chip) (light\$3 near3 emitt\$3))) & (thermal near3 expansion)	EPO; JPO;	
		(Chermar hears expansion)	DERWENT;	
			IBM TDB	
9	503	(((GaN nitride) & (semiconductor & (LED\$1	USPAT;	2004/11/08 13:40
		near3 chip) (light\$3 near3 emitt\$3))) &	US-PGPUB;	
		(thermal near3 expansion)) & solder\$3	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
10	463	((((GaN nitride) & (semiconductor & (LED\$1	USPAT;	2004/11/08 13:40
		near3 chip) (light\$3 near3 emitt\$3))) &	US-PGPUB;	
		(thermal near3 expansion)) & solder\$3) &	EPO; JPO;	
		substrate	DERWENT; IBM TDB	
11	371	(((((GaN nitride) & (semiconductor &	USPAT;	2004/11/08 13:29
1 **	371	(LED\$1 near3 chip) (light\$3 near3	US-PGPUB;	2004/11/00 13.23
		emitt\$3))) & (thermal near3 expansion)) &	EPO; JPO;	
		solder\$3) & substrate) & higher	DERWENT;	
		, , , , , , , , , , , , , , , , , , , ,	IBM_TDB	
12	39	(((((GaN nitride) & (semiconductor &	USPĀT;	2004/11/08 13:38
		(LED\$1 near3 chip) (light\$3 near3	US-PGPUB;	
1		emitt\$3))) & (thermal near3 expansion)) &	EPO; JPO;	
		solder\$3) & substrate) & higher) &	DERWENT;	,
1,2	00	((thermal near3 expansion) with higher)	IBM_TDB	2004/11/00 12:20
13	90	, T. T	USPAT;	2004/11/08 13:39
		substrate))	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
14	81	(LED\$1 with chip) (light\$3 near3 emitt\$3)	USPAT;	2004/11/08 13:39
		& (semiconductor & (chip with (GaN near5	US-PGPUB;	
		substrate)))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
15	28		USPAT;	2004/11/08 13:40
		& (semiconductor & (chip with (GaN near5	US-PGPUB;	
1		substrate)))) & (thermal near3 expansion)	EPO; JPO;	,
1			DERWENT;	
1.6	İ	///TRR01	IBM_TDB	2004/11/00 12 12
16	28		USPAT;	2004/11/08 13:40
		emitt\$3) & (semiconductor & (chip with	US-PGPUB;	
		(GaN near5 substrate)))) & (thermal near3 expansion)) & substrate	EPO; JPO; DERWENT;	
		copaniston, a substrate	IBM TDB	
L	<u> </u>		T T T T D D	

17	11	((((LED\$1 with chip) (light\$3 near3 emitt\$3) & (semiconductor & (chip with	USPAT; US-PGPUB;	2004/11/08 13:49
		(GaN near5 substrate)))) & (thermal near3	EPO; JPO;	
		expansion)) & substrate) & solder\$3	DERWENT;	
1.0		(/78801	IBM_TDB	2004/11/00 12.52
18	6	((LED\$1 with chip) (light\$3 near3 emitt\$3) & (semiconductor & (chip with (GaN near5	USPAT; US-PGPUB;	2004/11/08 13:52
		substrate)))) & ((mount\$3 submount\$3) with	EPO; JPO;	
		(thermal near3 expansion) with substrate)	DERWENT;	
			IBM_TDB	
19	8		USPAT;	2004/11/08 13:56
		& (semiconductor & (chip with (GaN near5 substrate)))) & ((mount\$3 submount\$3) same	US-PGPUB; EPO; JPO;	
		(thermal near3 expansion) same substrate)	DERWENT;	
•		,	IBM_TDB	
20	9	,	USPAT;	2004/11/08 13:58
		substrate))) & ((mount\$3 submount\$3) same (thermal near3 expansion) same substrate)	US-PGPUB; EPO; JPO;	
		(thermal hears expansion) same substrate)	DERWENT;	
			IBM TDB	
21	22		USPĀT;	2004/11/08 14:17
		substrate))) & ((mount\$3 submount\$3) &	US-PGPUB;	
		(thermal near3 expansion) & substrate)	EPO; JPO; DERWENT;	
			IBM TDB	
22	127803	semiconductor with laser	USPĀT;	2004/11/08 14:17
			US-PGPUB;	
			EPO; JPO; DERWENT;	
		·.	IBM TDB	
23	5486	((GaN nitride) with substrate) &	USPĀT;	2004/11/08 14:36
		(semiconductor with laser)	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
24	4157	((GaN nitride) near7 substrate) &	USPĀT;	2004/11/08 14:41
		(semiconductor with laser)	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
25	658	(((GaN nitride) near7 substrate) &	USPAT;	2004/11/08 14:19
		(semiconductor with laser)) & (thermal	US-PGPUB;	
		near3 expansion)	EPO; JPO; DERWENT;	
			IBM TDB	
26	15	(((GaN nitride) near7 substrate) &	USPĀT;	2004/11/08 14:37
		(semiconductor with laser)) & ((thermal	US-PGPUB;	
		near3 expansion) with higher with substrate)	EPO; JPO; DERWENT;	
		5425614667	IBM TDB	
27	10242	((GaN nitride) & substrate) &	USPĀT;	2004/11/08 14:37
ļ		(semiconductor with laser)	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
28	0	(((GaN nitride) & substrate) &	USPAT;	2004/11/08 14:38
		(semiconductor with laser)) & ((thermal	US-PGPUB;	
		near3 expansion) with (higher near7 than) with substrate)	EPO; JPO; DERWENT;	
			IBM TDB	
29	0	(semiconductor with laser) & ((thermal	USPĀT;	2004/11/08 14:39
		near3 expansion) with (higher near7 than)	US-PGPUB;	
		with substrate)	EPO; JPO; DERWENT;	
			IBM TDB	
30	0	semiconductor & ((thermal near3 expansion)	USPAT;	2004/11/08 14:39
		with (higher near7 than) with substrate)	US-PGPUB;	1
			EPO; JPO; DERWENT;	
L			IBM_TDB	
				· _ · · · · · · · · · · · · · · · · · ·

31	0	((thermal near3 expansion) with (higher	USPAT;	2004/11/08 14:40
		near7 than) with substrate)	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
32	0	((thermal near3 expansion) with (higher	USPAT;	2004/11/08 14:40
		adj than) with substrate)	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
33	824	((thermal near3 expansion) with (higher)	USPAT;	2004/11/08 14:40
	02.	with substrate)	US-PGPUB;	3001, 22 , 11
			EPO; JPO;	
			DERWENT;	
	4.0		IBM_TDB	0004/11/00 14:40
34	49	(semiconductor with laser) & (((thermal near3 expansion) with (higher) with	USPAT; US-PGPUB;	2004/11/08 14:40
		substrate))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
35	15	((GaN nitride) near7 substrate) &	USPAT;	2004/11/08 14:41
		((semiconductor with laser) & (((thermal	US-PGPUB;	
		near3 expansion) with (higher) with substrate)))	EPO; JPO; DERWENT;	
		Substrace///	IBM TDB	
-	1422619	semiconductor	USPAT;	2004/11/07 17:14
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	500623	LED\$1 (light\$3 near3 emitt\$3 near3 (diod\$3	IBM_TDB USPAT;	2004/11/07 17:16
	300023	device))	US-PGPUB;	2001, 11, 01 11.10
			EPO; JPO;	
			DERWENT;	
	70015		IBM_TDB	2004/11/07 17-16
_	79815	<pre>semiconductor & (LED\$1 (light\$3 near3 emitt\$3 near3 (diod\$3 device)))</pre>	USPAT; US-PGPUB;	2004/11/07 17:16
		emittys means (drodys device//)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	33299	(semiconductor & (LED\$1 (light\$3 near3 emitt\$3 near3 (diod\$3 device)))) & laser	USPAT; US-PGPUB;	2004/11/07 17:17
		emitt53 hears (diod\$3 device)))) & laser	EPO; JPO;	
		·	DERWENT;	
			IBM_TDB	
_	3281	semiconductor near3 laser near3 chip	USPAT;	2004/11/07 17:17
-			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	708	and the contract of the contra	USPAT;	2004/11/07 17:18
1		emitt\$3 near3 (diod\$3 device)))) & laser)	US-PGPUB;	
		& (semiconductor near3 laser near3 chip)	EPO; JPO; DERWENT;	
			IBM TDB	
_	41968	(semiconductor & (LED\$1 (light\$3 near3	USPAT;	2004/11/07 17:19
		emitt\$3 near3 (diod\$3 device)))) &	US-PGPUB;	
		substrat\$3	EPO; JPO;	
			DERWENT;	
_	11793	((semiconductor & (LED\$1 (light\$3 near3	IBM_TDB USPAT;	2004/11/07 17:45
	11,75	emitt\$3 near3 (diod\$3 device)))) &	US-PGPUB;	
		substrat\$3) & nitride	EPO; JPO;	
			DERWENT;	
_	157	(((semiconductor & (LED\$1 (light\$3 near3	IBM_TDB USPAT;	2004/11/07 17:20
	15/	emitt\$3 near3 (diod\$3 device)))) &	US-PGPUB;	2004/11/0/ 1/.20
		substrat\$3) & nitride) & (substrat\$3 with	EPO; JPO;	
		(thermal near3 expans\$4) with high\$3)	DERWENT;	
			IBM TDB	

		- /+		0004/11/07 17 02
-	156	((((semiconductor & (LED\$1 (light\$3 near3	USPAT; US-PGPUB;	2004/11/07 17:23
		<pre>emitt\$3 near3 (diod\$3 device)))) & substrat\$3) & nitride) & (substrat\$3 with</pre>	EPO; JPO;	
		(thermal near3 expans\$4) with high\$3)) &	DERWENT;	
		(layer\$1 stack\$3 chip\$3)	IBM TDB	
_	41	(((((semiconductor & (LED\$1 (light\$3 near3	USPAT;	2004/11/07 17:45
		emitt\$3 near3 (diod\$3 device))) &	US-PGPUB;	
		substrat\$3) & nitride) & (substrat\$3 with	EPO; JPO;	
		(thermal near3 expans\$4) with high\$3)) &	DERWENT;	
		(layer\$1 stack\$3 chip\$3)) & solder\$3	IBM_TDB	
-	7	(((((semiconductor & (LED\$1 (light\$3 near3	USPAT;	2004/11/07 17:47
		emitt\$3 near3 (diod\$3 device)))) &	US-PGPUB;	
		substrat\$3) & nitride) & (substrat\$3 with	EPO; JPO;	
		(thermal near3 expans\$4) with high\$3)) & solder\$3) & ((nitri\$3 near3 bas\$3)	DERWENT; IBM TDB	
		nitridebased)	101100	
_	7	(((((semiconductor & (LED\$1 (light\$3 near3	USPAT;	2004/11/07 17:47
	,	emitt\$3 near3 (diod\$3 device)))) &	US-PGPUB;	2001, 21, 01 27, 11
		substrat\$3) & nitride) & (substrat\$3 with	EPO; JPO;	
		(thermal near3 expans\$4) with high\$3)) &	DERWENT;	
		solder\$3) & ((nitri\$3 near3 bas\$3)	IBM_TDB	
		(nitride-based))	_	
_	41		USPAT;	2004/11/08 10:46
		emitt\$3 near3 (diod\$3 device)))) &	US-PGPUB;	
		substrat\$3) & nitride) & (substrat\$3 with	EPO; JPO;	
		(thermal near3 expans\$4) with high\$3)) & solder\$3	DERWENT; IBM TDB	
	1441160	solder\$3	USPAT;	2004/11/08 10:47
-	1441160	Semiconductoras	US-PGPUB;	2004/11/06 10.4/
			EPO; JPO;	
			DERWENT;	
	į		IBM TDB	:
_	422761	light\$3 near3 emitt\$3	USPĀT;	2004/11/08 10:48
		·	US-PGPUB;	
		·	EPO; JPO;	
			DERWENT;	
	95809	semiconductor\$3 & (light\$3 near3 emitt\$3)	IBM_TDB USPAT;	2004/11/08 10:48
_	93609	Semiconductor43 & (lighte43 hears emitte43)	US-PGPUB;	2004/11/08 10.48
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	493	(semiconductor\$3 & (light\$3 near3	USPĀT;	2004/11/08 10:49
		emitt\$3)) & (higher same (thermal near3	US-PGPUB;	
		expansion))	EPO; JPO;	
			DERWENT;	
	140	//gomigondugtores / /lightes mages	IBM_TDB	2004/11/08 10:52
-	140	((semiconductor\$3 & (light\$3 near3 emitt\$3)) & (higher same (thermal near3	USPAT; US-PGPUB;	2004/11/08 10:52
	1	expansion))) & (GaN (nitride adj bas\$3))	EPO; JPO;	
		companion of the country of the coun	DERWENT;	
			IBM TDB	
-	136	(((semiconductor\$3 & (light\$3 near3	USPAT;	2004/11/08 10:52
		emitt\$3)) & (higher same (thermal near3	US-PGPUB;	
		expansion))) & (GaN (nitride adj bas\$3)))	EPO; JPO;	
		& substrate	DERWENT;	
		(/	IBM_TDB	2004/11/00 10 52
-	94		USPAT;	2004/11/08 10:53
		<pre>emitt\$3)) & (higher same (thermal near3 expansion))) & ((GaN (nitride adj bas\$3))</pre>	US-PGPUB; EPO; JPO;	
		with substrate)	DERWENT;	
		Tion bubbliaco,	IBM TDB	
_	94	(((semiconductor\$3 & (light\$3 near3	USPAT;	2004/11/08 10:54
		emitt\$3)) & (higher same (thermal near3	US-PGPUB;	
		expansion))) & ((GaN (nitride adj bas\$3))	EPO; JPO;	
		with substrate)) & (layer\$1 chip\$3)	DERWENT;	
l	<u></u>		IBM_TDB	

	17	((((semiconductor\$3 & (light\$3 near3	USPAT;	2004/11/08 11:25
-	17	emitt\$3)) & (higher same (thermal near3	US-PGPUB;	2004/11/06 11:25
			EPO; JPO;	
		expansion))) & ((GaN (nitride adj bas\$3))	1 '	
		with substrate)) & (layer\$1 chip\$3)) &	DERWENT;	
	7	solder\$3	IBM_TDB	2004/11/09 11.26
_	/	"6326638"	USPAT;	2004/11/08 11:26
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	"6326638" & (thermal near3 expension)	USPAT;	2004/11/08 11:26
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		•	IBM_TDB	
-	2	"6326638" & solder\$3	USPAT;	2004/11/08 11:27
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	2	("6326638" & solder\$3) & substrate	USPAT;	2004/11/08 13:25
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	